AH116

½ W High Linearity InGaP HBT Amplifier

Product Features

- 800 – 1000 MHz
- 17.5 dB Gain @ 900 MHz
- +28 dBm P1dB
- +43 dBm Output IP3
- +5V Single Positive Supply
- Lead-free/green/RoHS-compliant SOIC-8 SMT Pkg.

Applications

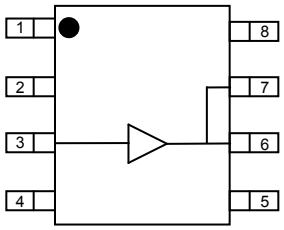
- Final stage amplifiers for Repeaters
- Mobile Infrastructure

Product Description

The AH116 is a high dynamic range driver amplifier in a low-cost surface mount package. The InGaP/GaAs HBT is able to achieve high performance for various narrow-band tuned application circuits with up to +43 dBm OIP3 and +28 dBm of compressed 1-dB power and is housed in a lead-free/green/RoHS-compliant SOIC-8 package. All devices are 100% RF and DC tested.

The product is targeted for use as driver amplifiers for wireless infrastructure where high linearity and medium power is required. The internal active bias allows the AH116 to maintain high linearity over temperature and operate directly off a +5 V supply. This combination makes the device an excellent fit for transceiver line cards and power amplifiers in current and next generation multi-carrier 3G base stations.

Functional Diagram



Function	Pin No.
Vref	1
Input	3
Output	6, 7
Vbias	8
GND	Backside Paddle
N/C or GND	2, 4, 5

Specifications (1)

Parameters	Units	Min	Typ	Max
Frequency Range	MHz		900	
Gain	dB	15	17.5	
Input R.L.	dB		18	
Output R.L.	dB		7	
Output P1dB	dBm	+27	+28.7	
Output IP3 (2)	dBm	+42	+43	
IS-95A Channel Power @ -45 dBc ACPR	dBm		+23	
Noise Figure	dB		7	
Operating Current Range (3)	mA	200	250	300
Device Voltage	V		+5	

1. Test conditions unless otherwise noted: 25 ºC, +5V supply, 900 MHz, in tuned application circuit.
2. 3OIP measured with two tones at an output power of +13 dBm/tone separated by 1 MHz. The suppression on the largest IM3 product is used to calculate the 3OIP using a 2:1 rule.
3. This corresponds to the quiescent current or operating current under small-signal conditions. It is expected that the current can increase up to 300mA at P1dB.

Typical Performance (1)

Parameters	Units	Typical
Frequency	MHz	900
Gain	dB	17.5
S11	dB	-18
S22	dB	-7
Output P1dB	dBm	+28.7
Output IP3 (2)	dBm	+43
IS-95A Channel Power @ -45 dBc ACPR	dBm	+23
Noise Figure	dB	7
Supply Bias		+5 V @ 250 mA

Not Recommended for New Designs

Recommended Replacement Part: TQP7M9102

Absolute Maximum Rating

Parameter	Rating
Storage Temperature	-65 to +150 °C
RF Input Power (continuous)	+22 dBm
Device Voltage	+8 V
Device Current	400 mA
Device Power	2 W
Thermal Resistance, Rth	62°C/W
Junction Temperature	+200°C

Junction Temperature for >10^6 hours MTTF

Operation of this device above any of these parameters may cause permanent damage.

Ordering Information

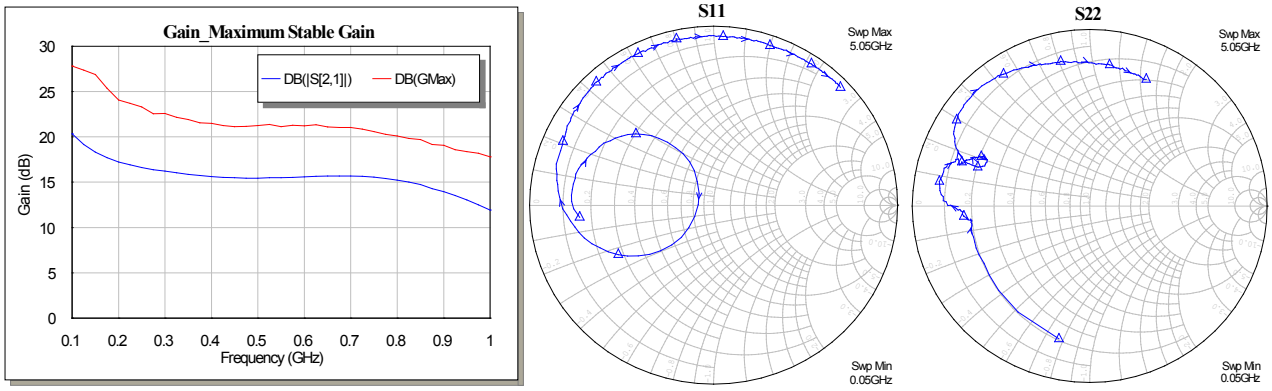
Part No.	Description
AH116-S8G	½ Watt, High Linearity InGaP HBT Amplifier (lead-free/green/RoHS-compliant SOIC-8 Pkg)

Standard tape / reel size = 500 pieces on a 7” reel

Specifications and information are subject to change without notice

Typical Device Data

S-Parameters (V_{cc} = +5 V, I_{cc} = 250 mA, T = 25 °C, calibrated to device leads)



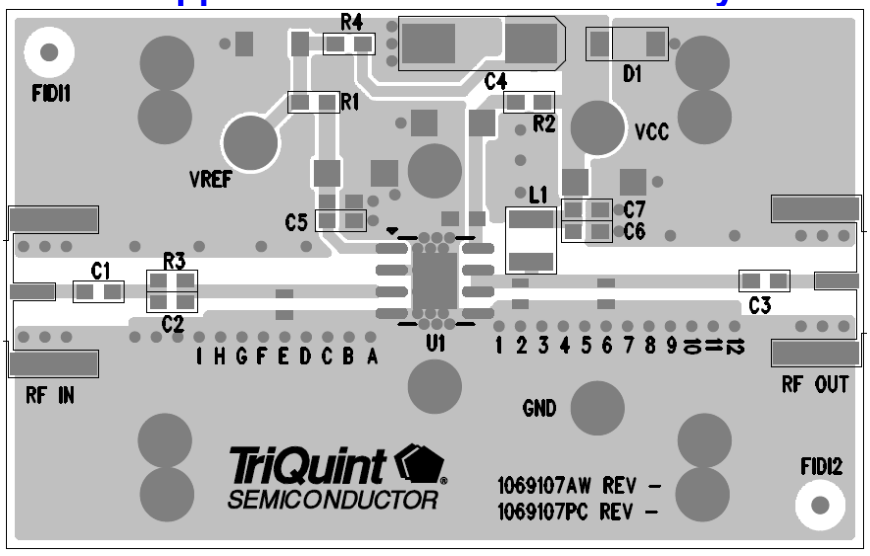
Notes:
The gain for the unmatched device in 50 ohm system is shown as the trace in black color. For a tuned circuit for a particular frequency, it is expected that actual gain will be higher, up to the maximum stable gain. The maximum stable gain is shown in the dashed red line.
The return loss plots are shown from 50 – 5050 MHz, with markers placed at 0.5 – 5.05 GHz in 0.5 GHz increments.

S-Parameters (V_{cc} = +5 V, I_{cc} = 250 mA, T = 25°C, unmatched 50 ohm system, calibrated to device leads)

Freq (MHz)	S11 (dB)	S21 (dB)	S21 (ang)	S12 (dB)	S12 (ang)	S22 (dB)	S22 (ang)
50	-2.72	24.16	133.35	-36.72	29.75	-2.23	-102.97
100	-2.25	20.33	124.95	-35.31	13.96	-3.08	-137.03
200	-2.31	17.23	119.37	-34.90	2.32	-3.32	-159.63
400	-3.08	15.63	98.28	-33.62	-16.36	-3.48	-172.70
600	-5.79	15.58	69.70	-32.10	-37.73	-2.87	-176.25
800	-19.72	15.22	25.60	-31.19	-78.95	-2.27	-179.74
1000	-6.06	11.91	-22.67	-33.26	-129.67	-1.40	173.15

Device S-parameters are available for download from the website at: http://www.tqs.com

Application Circuit PC Board Layout

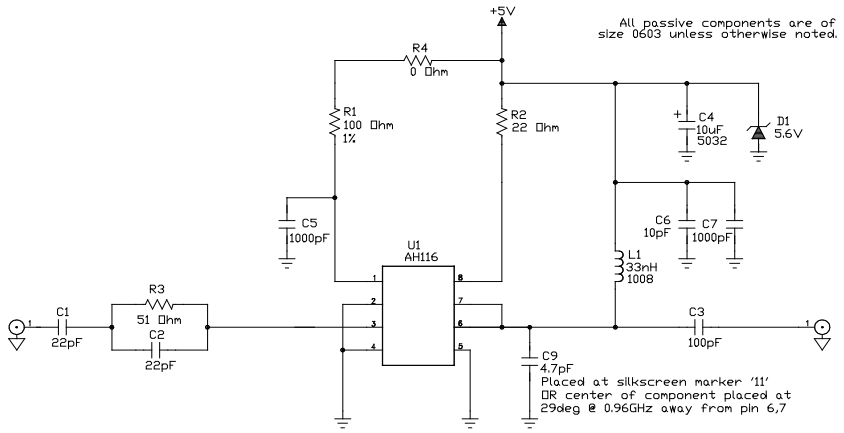


Circuit Board Material: .014" Getek, 4 - layer, 1 oz copper, Microstrip line details: width = .026", spacing = .026"
The silk screen markers 'A', 'B', 'C', etc. and '1', '2', '3', etc. are used as placemarkers for the input and output tuning Shunt capacitors – C8 and C9. The markers and vias are spaced in .050" increments.

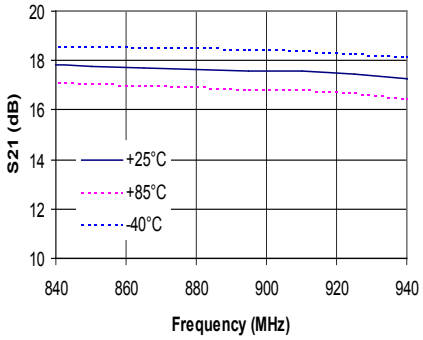
900 MHz Application Circuit (AH116-S8PCB900)

Typical RF Performance at 25 °C

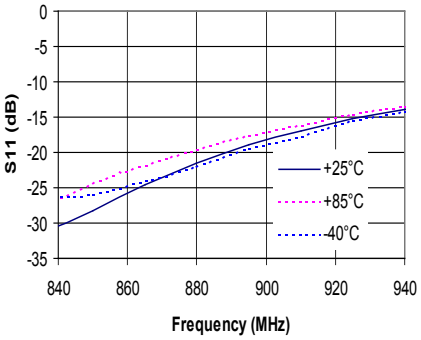
Frequency	900 MHz
S21 – Gain	17.5 dB
S11 – Input Return Loss	-18 dB
S22 – Output Return Loss	-7 dB
Output P1dB	+28.7 dBm
Output IP3 (+17 dBm / tone, 1 MHz spacing)	+43 dBm
Channel Power (@-45 dBc ACPR, IS-95 9 channels fwd)	+23 dBm
Noise Figure	7 dB
Device / Supply Voltage	+5 V
Quiescent Current	250 mA



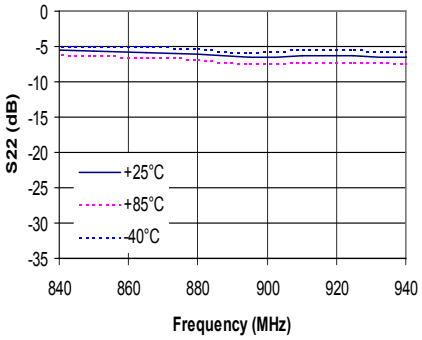
S21 vs Frequency



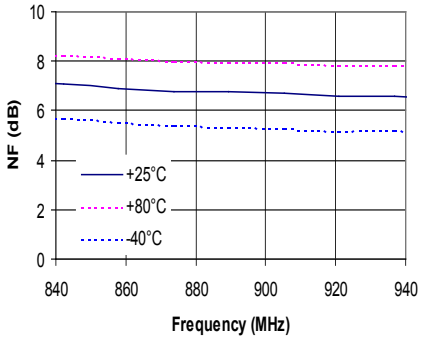
S11 vs. Frequency



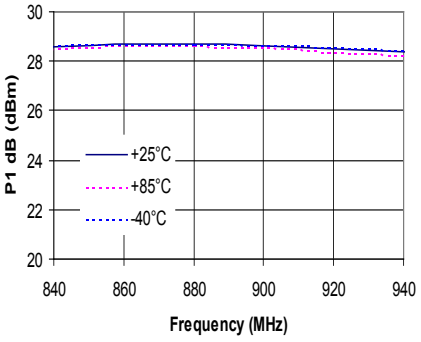
S22 vs. Frequency



Noise Figure vs. Frequency

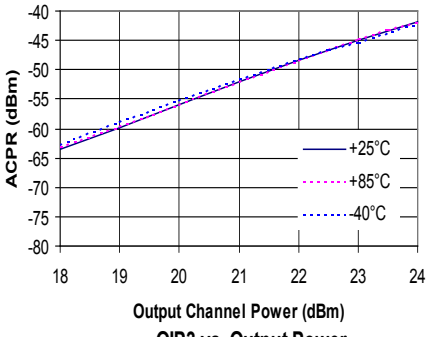


P1 dB vs. Frequency



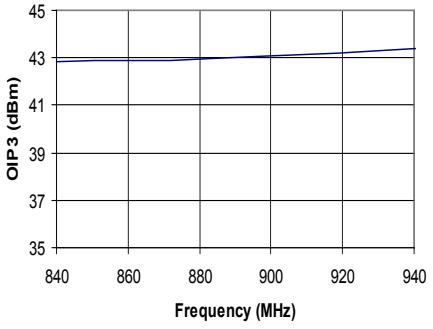
ACPR vs. Channel Power

IS-95, 9 Ch. Fwd, ±885KHz Meas BW, 900 MHz



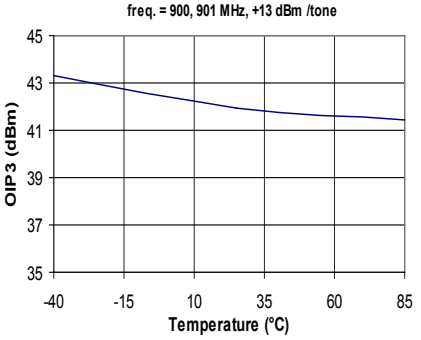
OIP3 vs. Frequency

+25°, +13 dBm / tone



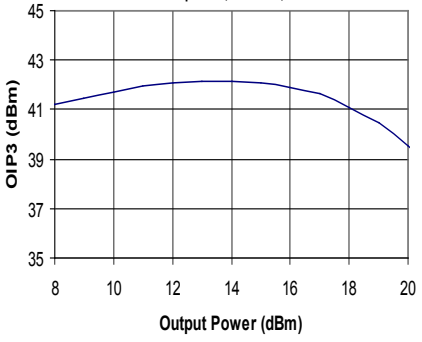
OIP3 vs. Temperature

freq. = 900, 901 MHz, +13 dBm /tone



OIP3 vs. Output Power

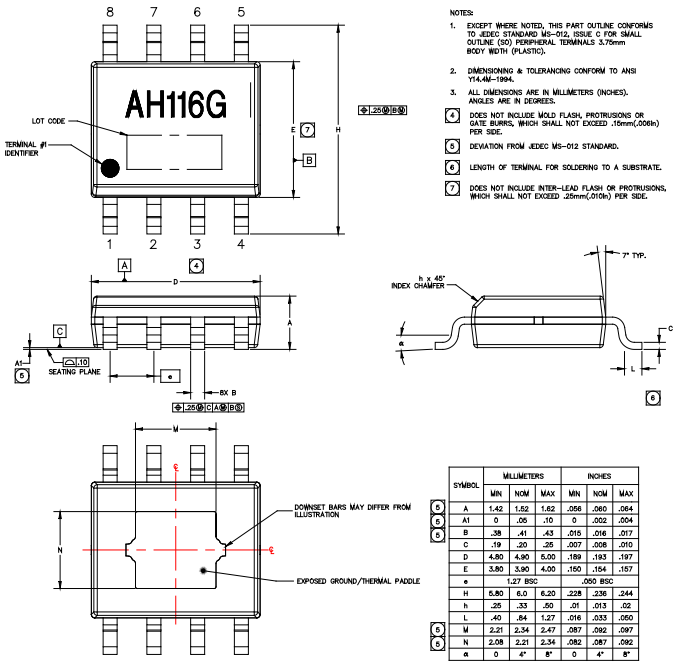
freq. = 900, 901 MHz, +25°C



AH116-S8G (Lead-Free Package) Mechanical Information

This package is lead-free/green/RoHS-compliant. The plating material on the leads is NiPdAu. It is compatible with both lead-free (maximum 260 °C reflow temperature) and lead (maximum 245 °C reflow temperature) soldering processes.

Outline Drawing



NOTES:
1. EXCEPT WHERE NOTED, THIS PART OUTLINE CONFORMS TO JEDEC STANDARD MS-012, ISSUE C FOR SMALL OUTLINE (SO) PERIPHERAL TERMINALS 3.75mm BODY WIDTH (PLASTIC).
2. DIMENSIONING & TOLERANCING CONFORM TO ANSI Y14.4M-1994.
3. ALL DIMENSIONS ARE IN MILLIMETERS (INCHES). ANGLES ARE IN DEGREES.
4. DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS, WHICH SHALL NOT EXCEED .15mm(.006in) PER SIDE.
5. DEVIATION FROM JEDEC MS-012 STANDARD.
6. LENGTH OF TERMINAL FOR SOLDERING TO A SUBSTRATE.
7. DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSIONS, WHICH SHALL NOT EXCEED .25mm(.010in) PER SIDE.

SYMBOL	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.42	1.52	1.62	.056	.060	.064
A1	0	.05	.10	0	.002	.004
B	.38	.41	.43	.015	.016	.017
C	.19	.20	.25	.007	.008	.010
D	4.80	4.90	5.00	.189	.193	.197
E	3.80	3.90	4.00	.150	.154	.157
e	1.27 BSC			.050 BSC		
H	5.80	6.0	6.20	.228	.236	.244
h	.25	.33	.50	.01	.013	.02
L	.40	.84	1.27	.016	.033	.050
M	2.21	2.34	2.47	.087	.092	.097
N	2.08	2.21	2.34	.082	.087	.092
α	0	4°	8°	0	4°	8°

Product Marking

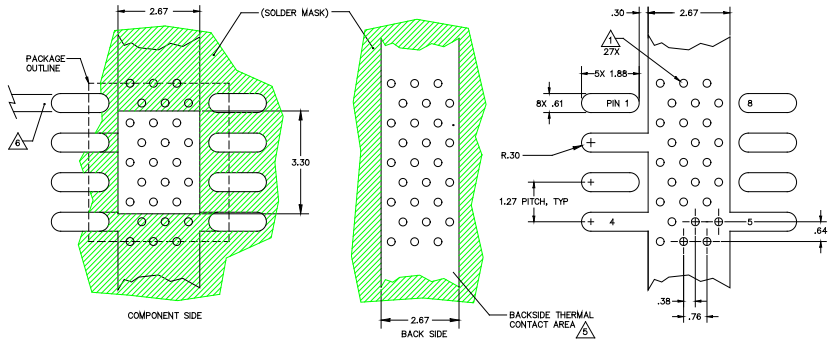
The component will be marked with an "AH116G" designator with an alphanumeric lot code on the top surface of the package.

ESD / MSL Information

Caution! ESD sensitive device.

ESD Rating:	Class 1B
Value:	Passes ⩾500V to <1000V
Test:	Human Body Model (HBM)
Standard:	JEDEC Standard JESD22-A114
MSL Rating:	Level 2 at +260 °C convection reflow
Standard:	JEDEC Standard J-STD-020

Mounting Configuration / Land Pattern



Mounting Config. Notes

1. Ground / thermal vias are critical for the proper performance of this device. Vias should use a .35mm (#80 / .0135") diameter drill and have a final plated thru diameter of .25 mm (.010").
2. Add as much copper as possible to inner and outer layers near the part to ensure optimal thermal performance.
3. Mounting screws can be added near the part to fasten the board to a heatsink. Ensure that the ground / thermal via region contacts the heatsink.
4. Do not put solder mask on the backside of the PC board in the region where the board contacts the heatsink.
5. RF trace width depends upon the PC board material and construction.
6. Use 1 oz. Copper minimum.
7. All dimensions are in millimeters (inches). Angles are in degrees.